L Number	Hits	Search Text	DB	Time stamp
1	8	("111" adj plane adj substrate) with (recess or hollow or groove or (cut adj out) or hole or via)	USPAT; US-PGPUB; EPO; JPO;	2004/03/01 15:02
2	0		DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/01 15:02
3	0	("111" adj plane) with (hollow near substrate)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/01 15:02
4	3	("111" adj plane) with (hollow with substrate)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/01 15:44
5	0	(soi adj (layer or film)) with (supporting adj substrate) with (crystal adj direction)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/01 15:45
6	1	(soi adj (layer or film)) with (substrate) with (crystal adj direction)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/01 15:46
7	3	(soi) with (substrate) with (crystal adj direction)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/01 16:36
8	0	(silicon adj "on" adj insulator) with (substrate) with (crystal adj direction)	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/01 15:51
9	0	(silicon adj "on" adj insulator) with (substrate) with (direction)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/01 15:51
10	299	(soi) with (substrate) with (direction)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/01 15:52
11	8	(soi) with (substrate) with (direction) with different	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/01 15:54
12	2	(soi) with (substrate) with (orientation) with different	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/01 15:54
13	37	(soi) with (substrate) with (crystal adj orientation)	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/01 15:56
14	141	crystal adj (direction or orientation) adj different	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/01 16:37
			IBM TDB	

				0004/02/03
15	3	(= 3 =)	USPAT;	2004/03/01
		adj different) and (soi with substrate)	US-PGPUB;	16:40
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
16	21	, , ,	USPAT;	2004/03/01
		adj different) and ((semiconductor adj	US-PGPUB;	16:55
		(layer or film)) with substrate)	EPO; JPO;	
		-	DERWENT;	
			IBM TDB	
17	l ol	crystal adj direction adj soi adj layer	USPĀT;	2004/03/01
			US-PGPUB;	16:55
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
18	51	anyatal adi direction adi substrate	USPAT;	2004/03/01
10	51	crystal adj direction adj substrate	· '	16:55
			US-PGPUB;	10:22
	i		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
19	1	' 2 ·· · · · · · · · · · · · · · · ·	USPAT;	2004/03/01
		soi	US-PGPUB;	17:09
			EPO; JPO;	,
			DERWENT;	
			IBM TDB	
20	0	contact adj plug adj extending adj	USPAT;	2004/03/01
		through adj oxide	US-PGPUB;	17:11
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
21	5	contact adj plug adj oxide	USPAT;	2004/03/01
	ا	contact adj prag adj onrde	US-PGPUB;	17:11
			EPO; JPO;	- /
			DERWENT;	
			IBM_TDB	2004/03/01
22	0	,	USPAT;	2004/03/01
		insulator)) adj (contact adj plug)	US-PGPUB;	17:12
1			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
23	1	(soi or (semiconductor adj "on" adj	USPAT;	2004/03/01
		insulator)) near (contact adj plug)	US-PGPUB;	17:13
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
24	32	(soi or (semiconductor adj "on" adj	USPAT;	2004/03/01
	[insulator)) with (contact adj plug)	US-PGPUB;	17:17
		,, ,, <u>,</u> ,	EPO; JPO;	
			DERWENT;	
			IBM TDB	
25	12	(soi or (semiconductor adj "on" adj	USPAT;	2004/03/01
	**	insulator)) with (contact adj via)	US-PGPUB;	17:18
		Institutor,, wrom (contact day via)	EPO; JPO;	= . • = 0
			DERWENT;	
1 20	000		IBM_TDB	2004/02/01
26	290	(soi or (semiconductor adj "on" adj	USPAT;	2004/03/01
		insulator)) with (contact adj hole)	US-PGPUB;	17:27
1			EPO; JPO;	
			DERWENT;	
_			IBM_TDB	
27	19	, , , ,	USPAT;	2004/03/01
		insulator)) with (contact adj opening)	US-PGPUB;	17:32
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
28	4	6229165.pn. and substrate	USPAT;	2004/03/01
1			US-PGPUB;	17:32
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
	I	l		·

				1 - 2 - 1 - 1 - 7
-	17		USPAT;	2004/03/01
		insulator)) and ((hollow or recessed) adj	US-PGPUB;	17:12
		substrate)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	514	(soi or (semiconductor adj "on" adj	USPĀT;	2004/02/26
	1	insulator)) and ((hollow or recessed)	US-PGPUB;	10:48
		with substrate)	EPO; JPO;	
		with substract,	DERWENT;	
			l :	!
			IBM_TDB	1 2004/02/26
_	40	(soi or (semiconductor adj "on" adj	USPAT;	2004/02/26
		insulator)) and ((cut adj out) with	US-PGPUB;	10:57
		substrate)	EPO; JPO;	
			DERWENT;	
	ļ		IBM_TDB	
<u>-</u>	225	((soi or (semiconductor adj "on" adj	USPAT;	2004/02/26
	i	insulator)) and ((via or hole or opening)	US-PGPUB;	11:16
		adj substrate)) and 257/\$.ccls.	EPO; JPO;	
	,	day babberaee,, and 20:,, 1:0021:	DERWENT;	
			IBM TDB	
	0071	057/247 3		2004/02/26
-	2071	257/347.ccls.	USPAT;	2004/02/26
			US-PGPUB;	15:17
			EPO; JPO;	
			DERWENT;	
			IBM_TDB]
-	205	257/348.ccls.	USPAT;	2004/02/26
1			US-PGPUB;	15:21
			EPO; JPO;	
		1	DERWENT;	
			IBM TDB	
	41-	257/2401-	_	2004/02/26
-	417	257/349.ccls.	USPAT;	1
			US-PGPUB;	15:29
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	930	257/350.ccls.	USPĀT;	2004/02/26
			US-PGPUB;	15:40
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
	F26	257/351.ccls.	USPAT;	2004/02/26
-	536	237/331.CCIS.		15:50
			US-PGPUB;	13:30
1			EPO; JPO;	
1			DERWENT;	
1	1		IBM_TDB	
-	380	257/352.ccls.	USPAT;	2004/02/26
1			US-PGPUB;	15:54
			EPO; JPO;	
			DERWENT;	
			IBM TDB	1
_	280	257/353.ccls.	USPAT;	2004/02/26
	200	2017303.0013.	US-PGPUB;	15:58
				±3.50
			EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
-	285	257/354.ccls.	USPAT;	2004/03/01
			US-PGPUB;	09:21
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	1	6084284.pn. and soi	USPAT;	2004/03/01
	1	OUT 120 1. pii. did DOI	US-PGPUB;	09:26
			· ·	"3.2"
			EPO; JPO;	
			DERWENT;	
		l	IBM_TDB	0004/00/01
-	1		USPAT;	2004/03/01
		adj layer)	US-PGPUB;	09:27
			EPO; JPO;	
/l			DERWENT;	1
1			IBM TDB	
1	1		<u> </u>	<u> </u>

	0	C004204 nn -nd /-ili-nn -di	USPAT;	2004/03/01
_	0		US-PGPUB;	09:28
		layer)		09:28
			EPO; JPO;	
			DERWENT;	1
		l	IBM_TDB	
_	1	6084284.pn. and (thick adj silicon)	USPAT;	2004/03/01
1]		US-PGPUB;	09:27
1			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	6084284.pn. and (support adj layer)	USPAT;	2004/03/01
	[US-PGPUB;	09:28
			EPO; JPO;]
1			DERWENT;	
			IBM_TDB	
-	1	6084284.pn. and (support)	USPAT;	2004/03/01
1			US-PGPUB;	10:23
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	280	substrate and (four adj faces)	USPAT;	2004/03/01
			US-PGPUB;	10:24
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	48	substrate with (four adj faces)	USPAT;	2004/03/01
			US-PGPUB;	10:33
1	1		EPO; JPO;	1
			DERWENT;	
			IBM TDB	
-	5	substrate with (four adj end adj faces)	USPAT;	2004/03/01
1]	US-PGPUB;	10:36
1			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	1188	substrate with ("111" adj plane)	USPAT;	2004/03/01
			US-PGPUB;	10:37
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	160	substrate with ("111" adj plane) with	USPĀT;	2004/03/01
		(recess or hollow or groove or (cut adj	US-PGPUB;	14:59
		out) or hole or via)	EPO; JPO;	
		040, 02 11020 02 024	DERWENT;	
			IBM TDB	